



# MMBTA44

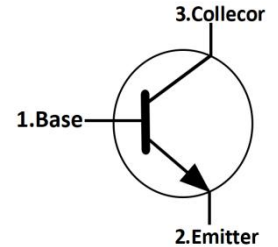
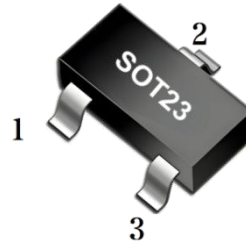
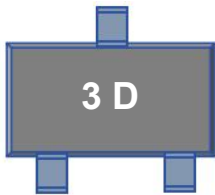
## NPN SILICON TRANSISTOR

### FEATURES

- \* High Collector-Emitter Voltage
- \* Complement to MMBTA94

### MARKING

Type Code: Marking: 3 D



### ABSOLUTE MAXIMUM RATINGS (Tc=25°C, unless otherwise specified)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	400	V
V <sub>CEO</sub>	Collector-emitter voltage	400	V
V <sub>EBO</sub>	Emitter-base voltage	6	V
I <sub>C</sub>	Collector Current-Continuous	200	mA
I <sub>CM</sub>	Collector Current -Pulsed	300	mA
P <sub>C</sub>	Collector Power Dissipation	350	mW
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C
θ <sub>JA</sub>	Thermal Resistance From Junction To Ambient	357	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA, I <sub>E</sub> =0	400		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO*</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	400		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6		V
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> =400V, I <sub>E</sub> =0		0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0		0.1	μA
DC Current Gain	h <sub>FE1*</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA	40		
	h <sub>FE2*</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	50	200	
	h <sub>FE3*</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA	45		
	H <sub>FE4*</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =100mA	40		
Collector-emitter saturation voltage	V <sub>CE(sat)*</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0.1mA		0.4	V
	V <sub>CE(sat)*</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.5	V
	V <sub>CE(sat)*</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA		0.75	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)*</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.75	V



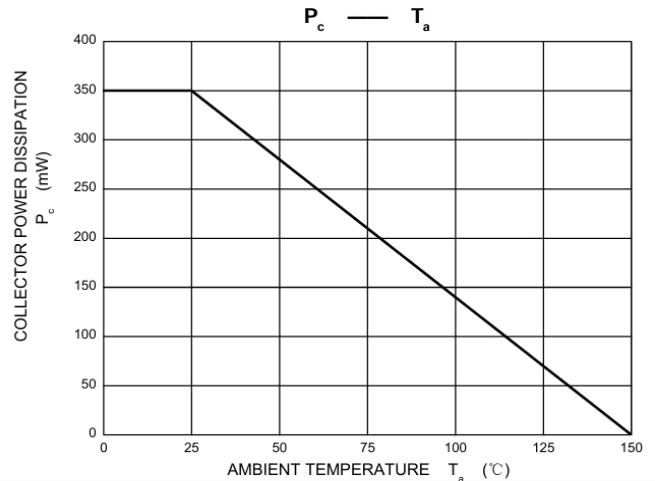
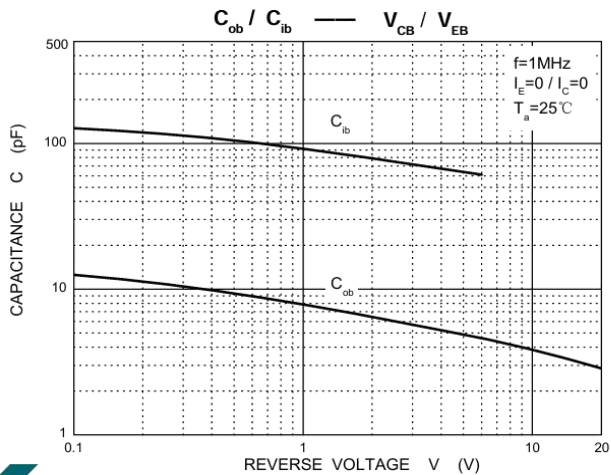
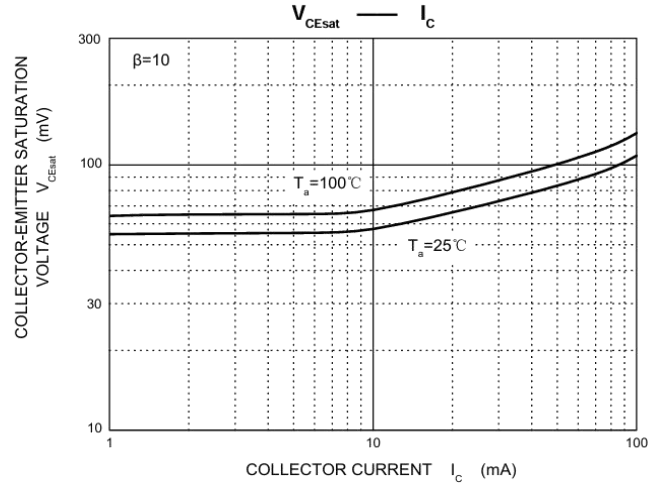
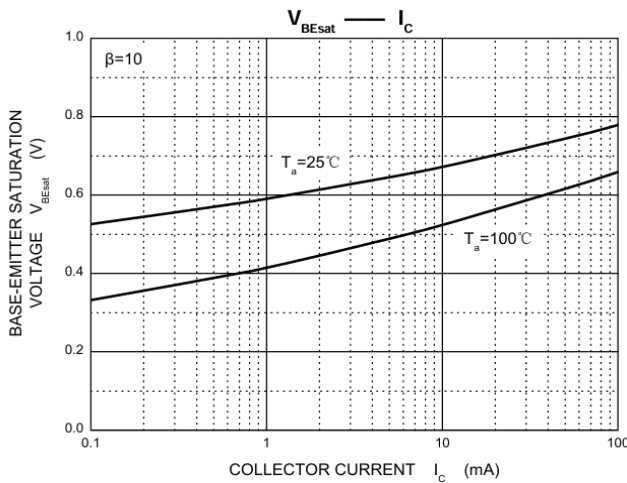
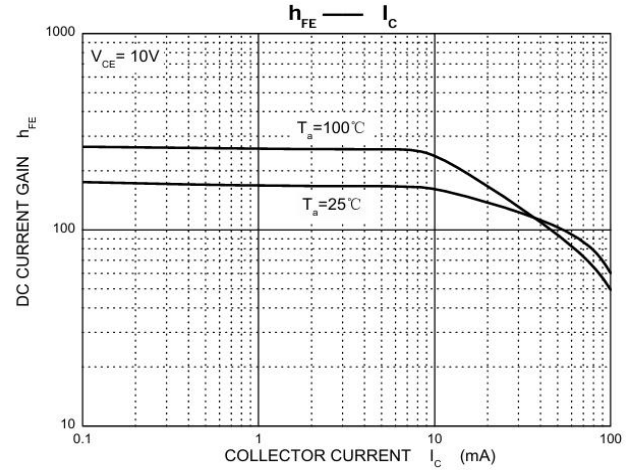
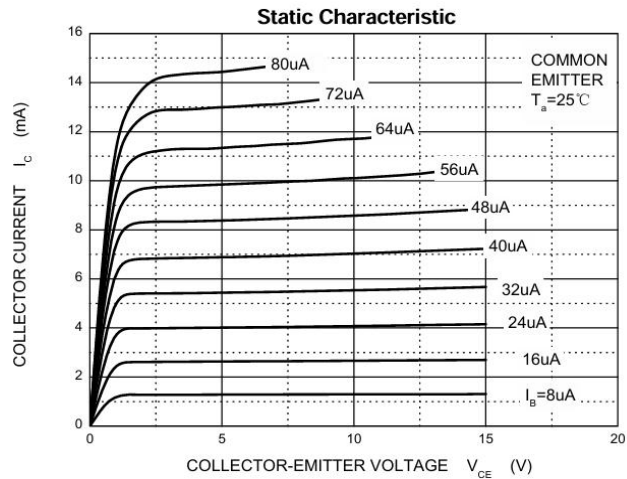
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# NPN SILICON TRANSISTOR

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
Collector output capacitance	$C_{ob}$	$V_{CB}=20V, I_E=0, f=1MHz$		7	pF
Emitter input capacitance	$C_{ib}$	$V_{EB}=0.5V, I_C=0, f=1MHz$		130	pF
Transition frequency	$f_T$	$V_{CE}=20V, I_C=10mA, f=30MHz$	50		MHz

\*Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2.0\%$ .

## TYPICAL CHARACTERISTICS





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# NPN SILICON TRANSISTOR

## SOT23 PACKAGE OUTLINE DIMENSIONS

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Note:  
1. Controlling dimension: in millimeters.  
2. General tolerance: ±0.05mm.  
3. The pad layout is for reference purposes only.

## REEL PACKING

Top cover tape thickness 0.10mm (0.004") max. thick

Embossed carrier tape

Trailer Tape 50±2 Empty Pockets

Components

Leader Tape 100±2 Empty Pockets

Dimensions are in millimeter										
PKG TYPE	A	B	C	d	E	F	Po	P	P1	W
SOT-23	3.15	2.77	1.22	Φ1.50	1.75	3.50	4.00	4.00	2.00	8.00
Reel Optiom	D	D1	D2	G	H	I	W1	W2	Q.TY PER REEL	
7" Dia	Φ178.0	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30	3000PCS	
13" Dia	φ330.0	/	13.00	/	/	R6.50	9.50	12.30	10000PCS	